

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
1	BRS	L1	4321	(SiC or "silicon carbide") same etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:43			0
2	BRS	L8	15703	CF4 or "carbon tetrafluoride" or "CF.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:09			0
3	BRS	L15	7504	CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:40			0
4	BRS	L22	1193	CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:39			0
5	BRS	L29	13906	CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:41			0
6	BRS	L36	956347	H2 or hydrogen or "H.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:42			0
7	BRS	L43	502173	NH3 or ammonia or "NH.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:42			0
8	BRS	L57	62	1 same 29	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:43			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
9	BRS	L64	174	1 same 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44			0
10	BRS	L71	0	50 same (36 or 43)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44			0
11	BRS	L78	8	57 same (36 or 43)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44			0
12	BRS	L92	4	(low adj3 ("k" or dielectric)) and 78	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:53			0
13	BRS	L99	10	(low adj3 ("k" or dielectric)) and 85	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:48			0
14	BRS	L106	186	("low k" or "low dielectric") same 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:15			0
15	BRS	L113	143	106 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:55			0
16	BRS	L120	43	106 not 113	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:15			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
17	BRS	L50	1	1 same 22	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:22			0
18	BRS	L85	40	64 same (36 or 43)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:27			0

92	4	(low adj3 ("k" or dielectric)) and (((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:53
99	10	(low adj3 ("k" or dielectric)) and (((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:48
106	186	("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:15
113	143	("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:55
120	43	("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) not (("low k" or "low dielectric") same ((SiC or "silicon carbide") same etch\$3)) and 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:15
50	1	((SiC or "silicon carbide") same etch\$3) same (CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 14:22

L Number	Hits	Search Text	DB	Time stamp
1	4321	(SiC or "silicon carbide") same etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:43
8	15703	CF4 or "carbon tetrafluoride" or "CF.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:09
15	7504	CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:40
22	1193	CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:39
29	13906	CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:41
36	956347	H2 or hydrogen or "H.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:42
43	502173	NH3 or ammonia or "NH.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:42
57	62	((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:43
64	174	((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44
71	0	((SiC or "silicon carbide") same etch\$3) same (CH2F2 or "carbon difluoride" or "difluoromethane" or "CH.sub.2 F.sub.2")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44
78	8	((SiC or "silicon carbide") same etch\$3) same (CHF3 or "carbon trifluoride" or "trifluorocarbon" or "CHF.sub.3" or "trifluoromethane")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:44
85	40	((SiC or "silicon carbide") same etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4")) same ((H2 or hydrogen or "H.sub.2") or (NH3 or ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 12:45

	Type	L #	Hits	Search Text	D B s	Ti me St a m p	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
1	BRS	L1	4 3 2 1	(SiC or "silicon carbide") same etch\$3	U S P A T; U S P P G P U B; E E P O; J P P O; D E R W E N T; I B M T D B	2 0 0 3/ 0 3/ 0 8 1 2: 4 3			0

	Type	L #	Hits	Search Text	D B s	Ti me St am p	C o m m e n t s	E r r o r s
2	BRS	L8	1 5 7 0 3	CF4 or "carbon tetrafluoride" or "CF.sub.4"	USPAT; USPPG PUB; EEP O; JPO; DDERW ENT; IBM TDB	2003/03/08 12:09		0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r m e s s a g e s	E r r o r m e s s a g e s
4	BRS	L22	200	(SiC or "silicon carbide") same (etch\$3) same (CF4 or "carbon tetrafluoride" or "CF.sub.4" or trifluoromethane or CHF3 or "CHF.sub.3" or difluoromethane or CH2F2 or "CH.sub.2 F.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/08 11:57			0